

Digital transistors (Includes resistors)

DTD133H□

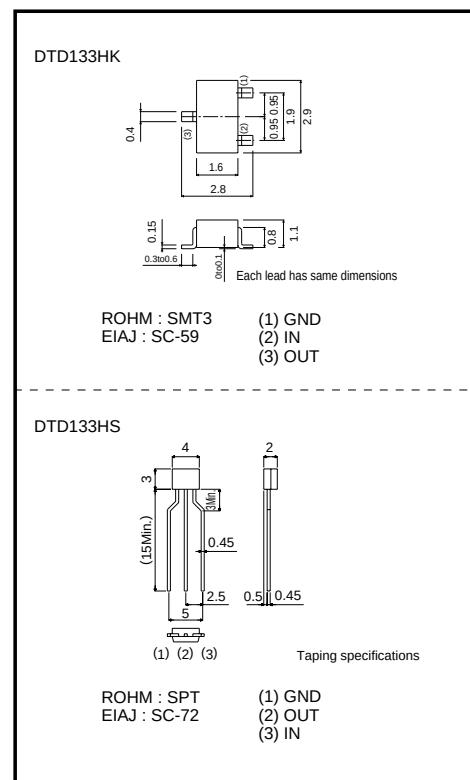
●Features

- 1) A built-in bias resistor allows inverter circuit configuration without external resistors for input (see equivalent circuit diagram).
- 2) The bias resistor consists of a thin-film resistor which is completely isolated, providing the capability to negative-bias the input, and avoiding parasitic effects.
- 3) Operation starts by simply setting On/Off conditions, simplifying the design of equipment using the transistors.
- 4) High packing density.

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Supply voltage	V_{CC}	50	V
Input voltage	V_I	-6~+20	V
Output current	I_C	500	mA
Power dissipation	DTD133HK	200	mW
	DTD133HS	300	
Junction temperature	T_J	150	°C
Storage temperature	T_{stg}	-55~+150	°C

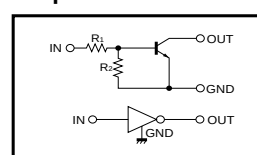
●External dimensions (Units : mm)



●Package, marking, and packaging specifications

Part No.	DTD133HK	DTD133HS
Package	SMT3	SPT
Marking	G08	-
Packaging code	T146	TP
Basic ordering unit (pieces)	3000	5000

●Equivalent circuit



●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	$V_{I(off)}$	-	-	0.5	V	$V_{CC}=5V$, $I_O=100\mu A$
	$V_{I(on)}$	2.0	-	-	V	$V_O=0.3V$, $I_O=20mA$
Output voltage	$V_{O(on)}$	-	0.1	0.3	V	$I_O=50mA$, $I_I=2.5mA$
Input current	I_I	-	-	2.4	mA	$V_I=5V$
Output current	$I_{O(off)}$	-	-	0.5	μA	$V_{CC}=50V$, $V_I=0V$
DC current gain	G_I	56	-	-	-	$I_O=50mA$, $V_O=5V$
Input resistance	R_1	-	3.3	-	$k\Omega$	-
Resistance ratio	R_2/R_1	2.4	3.0	3.7	-	-
Transition frequency	f_T	-	200	-	MHz	$V_{CE}=10V$, $I_E=-5mA$, $f=100MHz$

*Transition frequency of the device.

Transistors

●Electrical characteristics curves

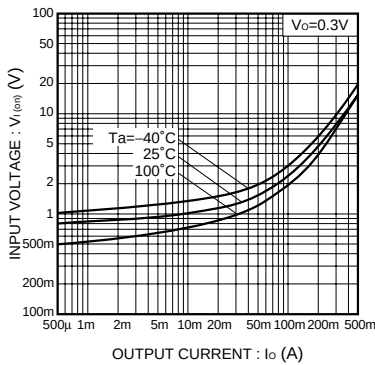


Fig.1 Input voltage vs. output current (ON characteristics)

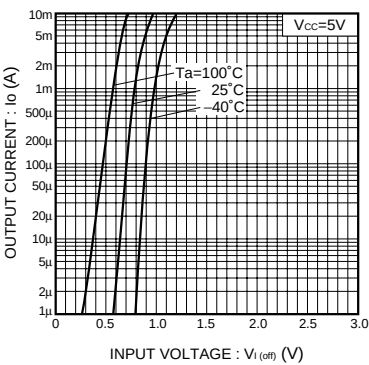


Fig.2 Output current vs. input voltage (OFF characteristics)

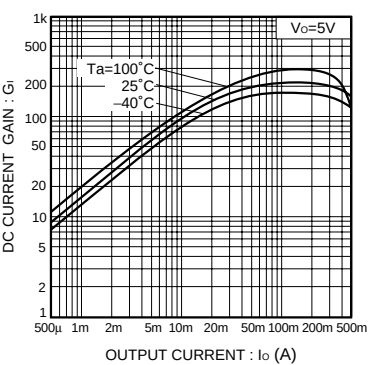


Fig.3 DC current gain vs. output current characteristics

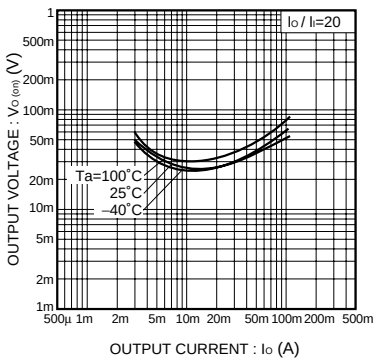


Fig.4 Output voltage vs. output current characteristics